DATA SHEET

74LVC125Quad buffer/line driver; 3-State

Product specification Supersedes data of February 1996 IC24 Data Handbook







74LVC125

FEATURES

- Wide supply voltage range of 1.2 to 3.6 V
- In accordance with JEDEC standard no. 8-1A
- Inputs accept voltages up to 5.5 V
- CMOS lower power consumption
- Direct interface with TTL levels
- Output drive capability 50 Ω transmission lines at 85°C

DESCRIPTION

The 74LVC125 is a high performance, low-power, low-voltage Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

The 74LVC125 consists of four non-inverting buffers/line drivers with 3-State outputs. The 3-State outputs (nY) are controlled by the output enable input (nOE). A HIGH at nOE causes the outputs to assume a high impedance OFF-state.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5 \text{ ns}$

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay nA to nY	C _L = 15 pF; V _{CC} = 3.3 V	3.5	ns
C _I	Input capacitance		5.0	pF
C _{PD}	Power dissipation capacitance per buffer	Notes 1 and 2	22	pF

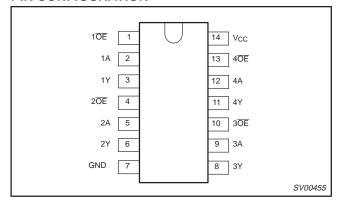
NOTES:

- 1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW) $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:
 - f_i = input frequency in MHz; C_L = output load capacity in pF;
- f_0 = output frequency in MHz; V_{CC} = supply voltage in V; Σ ($C_L \times V_{CC}^2 \times f_0$) = sum of the outputs. 2. The condition is V_I = GND to V_{CC}

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic SO	-40°C to +85°C	74LVC125 D	74LVC125 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74LVC125 DB	74LVC125 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74LVC125 PW	74LVC125PW DH	SOT402-1

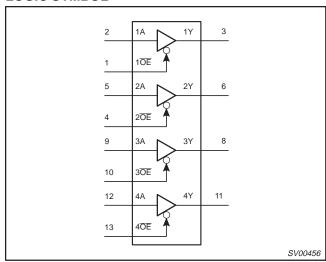
PIN CONFIGURATION



PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	1 OE – 4 OE	Data enable inputs (active LOW)
2, 5, 9, 12	1A – 4A	Data inputs
3, 6, 8, 11	1Y – 4Y	Data Outputs
7	GND	Ground (0 V)
14	V _{CC}	Positive supply voltage

LOGIC SYMBOL



74LVC125

FUNCTION TABLE

INP	OUTPUT	
nŌĒ	nA	nY
L	L	L
L	Н	Н
Н	X	Z

NOTES:

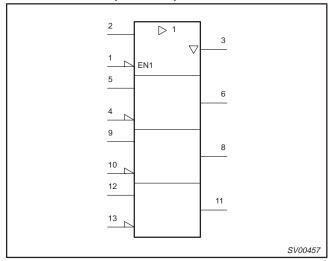
H = HIGH voltage level

L = LOW voltage level

X = don't care

Z = high impedance OFF-state

LOGIC SYMBOL (IEEE/IEC)



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	LIM	UNIT	
STIVIBUL	PARAMETER	CONDITIONS	MIN	MAX	UNII
V _{CC}	DC supply voltage (for max. speed performance)		2.7	3.6	V
V _{CC}	DC supply voltage (for low-voltage applications)		1.2	3.6	V
V _I	DC input voltage range		0	5.5	V
V _{I/O}	DC input voltage range for I/Os		0	V _{CC}	V
V _O	DC output voltage range		0	V _{CC}	V
T _{amb}	Operating free-air temperature range		-40	+85	°C
t _r , t _f	Input rise and fall times	$V_{CC} = 1.2 \text{ to } 2.7V$ $V_{CC} = 2.7 \text{ to } 3.6V$	0 0	20 10	ns/V

ABSOLUTE MAXIMUM RATINGS¹

In accordance with the Absolute Maximum Rating System (IEC 134). Voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +6.5	V
I _{IK}	DC input diode current	$V_I < 0$	-50	mA
VI	DC input voltage	Note 2	-0.5 to +5.5	V
V _{I/O}	DC input voltage range for I/Os		-0.5 to V _{CC} +0.5	V
I _{OK}	DC output diode current	$V_O > V_{CC}$ or $V_O < 0$	±50	mA
V _{OUT}	DC output voltage	Note 2	-0.5 to V _{CC} +0.5	V
I _{OUT}	DC output source or sink current	$V_O = 0$ to V_{CC}	±50	mA
I _{GND} , I _{CC}	DC V _{CC} or GND current		±100	mA
T _{stg}	Storage temperature range		–60 to +150	°C
P _{TOT}	Power dissipation per package – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	500 500	mW

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the
 device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
 absolute-maximum-rated conditions for extended periods may affect device reliability.
- 2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

Philips Semiconductors Product specification

Quad buffer/line driver; 3-State

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DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

				L	IMITS		UNIT
SYMBOL	PARAMETER	TEST CONDITIO	NS	Temp = -	40°C to ⋅	+85°C	
			MIN	TYP ¹	MAX	1	
V	HICH level leput voltage	V _{CC} = 1.2V		V _{CC}			V
V _{IH}	HIGH level Input voltage	V _{CC} = 2.7 to 3.6V		2.0			
V	LOW lovel length veltage	V _{CC} = 1.2V				GND	V
V _{IL}	LOW level Input voltage	V _{CC} = 2.7 to 3.6V				0.8	
		$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 0.000$	= -12mA	V _{CC} - 0.5			
.,	LUCLUS and authority valtages	$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $I_O = 0.00$	V _{CC} -0.2	V _{CC}			
V _{OH}	HIGH level output voltage	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 0.000$	V _{CC} -0.6			1	
		$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $I_O =$	= –24mA	V _{CC} - 1.0			
		$V_{CC} = 2.7V$; $V_I = V_{IH}$ or V_{IL} ; $I_O = 0.00$	= 12mA			0.40	
V _{OL}	LOW level output voltage	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O$	= 100μΑ		GND	0.20	V
		$V_{CC} = 3.0V$; $V_I = V_{IH}$ or V_{IL} ; $I_O =$	= 24mA			0.55	
l _l	Input leakage current	$V_{CC} = 3.6V$; $V_I = 5.5V$ or GND	Not for I/O pins		±0.1	±5	μΑ
I _{IHZ} /I _{ILZ}	Input current for common I/O pins	$V_{CC} = 3.6V$; $V_I = V_{CC}$ or GND			± 0.1	±15	μΑ
l _{OZ}	3-State output OFF-state current	$V_{CC} = 3.6V$; $V_I = V_{IH}$ or V_{IL} ; V_O	= V _{CC} or GND		0.1	±10	μΑ
I _{CC}	Quiescent supply current	$V_{CC} = 3.6V; V_{I} = V_{CC} \text{ or GND; I}$		0.1	20	μΑ	
Δl _{CC}	Additional quiescent supply current per input pin	$V_{CC} = 2.7V \text{ to } 3.6V; V_I = V_{CC} - 400$		5	500	μΑ	

NOTE:

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^{1.} All typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

AC CHARACTERISTICS

GND = 0 V; $t_r = t_f = 2.5$ ns; $C_L = 50$ pF; $R_L = 500\Omega$; $T_{amb} = -40$ °C to +85°C.

				LIMITS							
SYMBOL PARAMETER		WAVEFORM	$V_{CC} = 3.3V \pm 0.3V$			٧	_{CC} = 2.7\	/	V _{CC} = 1.2V	UNIT	
			MIN	TYP ¹	MAX	MIN	TYP	MAX	TYP		
t _{PHL} t _{PLH}	Propagation delay nA to nY	Figure 1, 3		3.5	6.5		3.9	7.0		ns	
t _{PZH}	3-state output enable time nOE to nY	Figure 2, 3		3.8	7.0		4.4	8.0		ns	
t _{PHZ}	3-state output disable time nOE to nY	Figure 2, 3		3.3	5.5		4.0	6.5		ns	

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NOTE:

AC WAVEFORMS

 V_M = 1.5 V at $V_{CC} \ge 2.7$ V

 $V_{M} = 0.5 \times V_{CC}$ at $V_{CC} < 2.7 \text{ V}$

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are the typical output voltage drop that occur with the output load.

 $V_X = V_{OL} + 0.3 \text{ V at } V_{CC} \ge 2.7 \text{ V};$

$$\begin{split} &V_X = V_{OL} + 0.1 \times V_{CC} \text{ at } V_{CC} < 2.7 \text{ V}; \\ &V_Y = V_{OH} - 0.3 \text{ V at } V_{CC} \ge 2.7 \text{ V}; \end{split}$$

 $V_Y = V_{OH} - 0.1 \times V_{CC}$ at $V_{CC} < 2.7$ V.

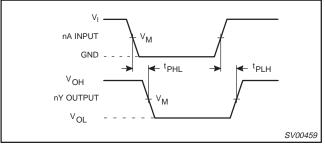


Figure 1. Input (nA) to output (nY) propagation delays.

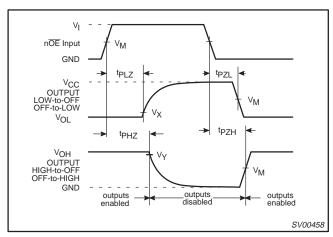


Figure 2. 3-State enable and disable times.

TEST CIRCUIT

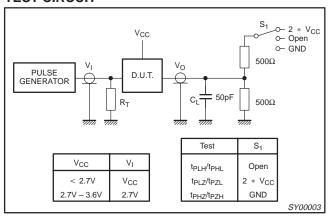


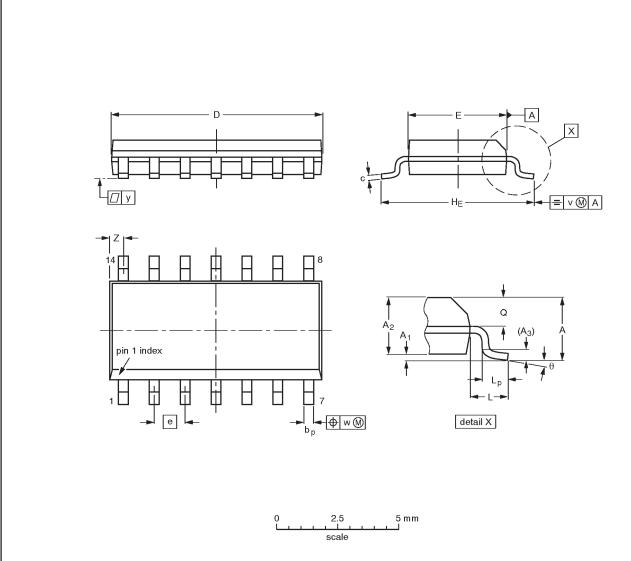
Figure 3. Load circuitry for switching times.

^{1.} These typical values are at V_{CC} = 3.3V and T_{amb} = 25°C.

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bp	c	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Ø	٧	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	1 // // // //	0.0098 0.0039		0.01		0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

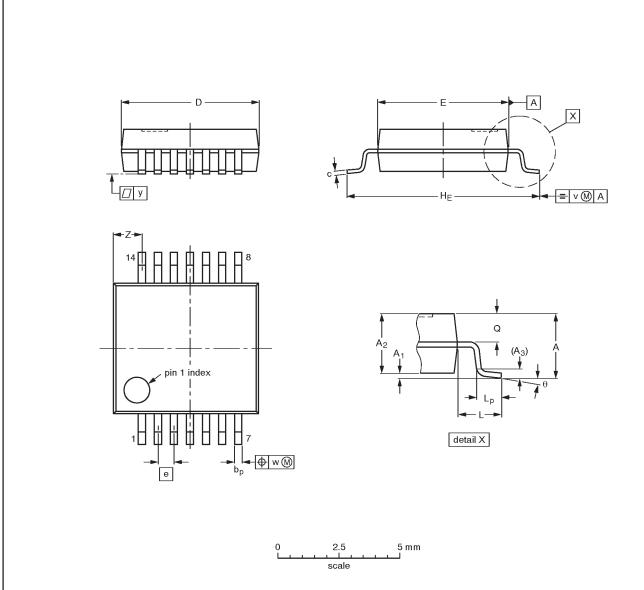
OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT108-1	076E06\$	MS-012AB			91-08-13 95-01-23

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	bp	c	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Ø	٧	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

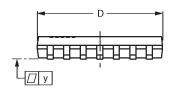
1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

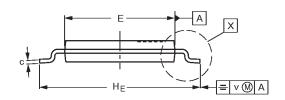
OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	PROJECTION	1330E DATE	
SOT337-1		MO-150AB			95-02-04 96-01-18

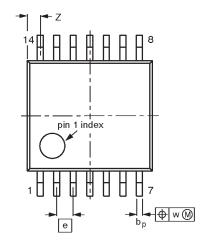
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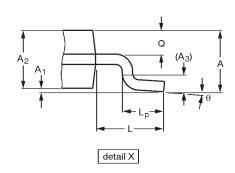
TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

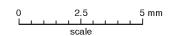
SOT402-1











DIMENSIONS (mm are the original dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bр	c	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				-94-07-12 95-04-04	

Philips Semiconductors Product specification

Quad buffer/line driver; 3-State

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NOTES

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DEFINITIONS						
Data Sheet Identification	Product Status	Definition				
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.				
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.				
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